

Transistors with Built-in Resistor DRC2124E0L

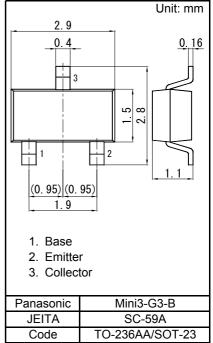
DRC2124E0L Silicon NPN epitaxial planar type

For digital circuits Complementary to DRA2124E

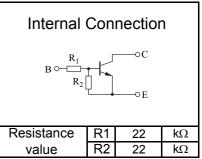
Features

- Low collector-emitter saturation voltage Vce(sat)
- Halogen-free / RoHS compliant (EU RoHS / UL-94 V-0 / MSL:Level 1 compliant)
- Marking Symbol: NE
- Packaging

Embossed type (Thermo-compression sealing): 3 000 pcs / reel (standard)



| mbol Rating | Unit |
|-----------------|-------------------------------------------------------------|
| CBO 50 | V |
| CEO 50 | V |
| IC 100 | mA |
| PT 200 | mW |
| Tj 150 | °C |
| opr -40 to +85 | °C |
| stg -55 to +150 | °C |
| | CBO 50 CEO 50 IC 100 PT 200 Tj 150 opr -40 to +85 |



| Electrical Characteristics | Ta = 25 °C ± 3 °C |
|----------------------------|-------------------|
|----------------------------|-------------------|

■ Absolute Maximum Ratings Ta = 25 °C

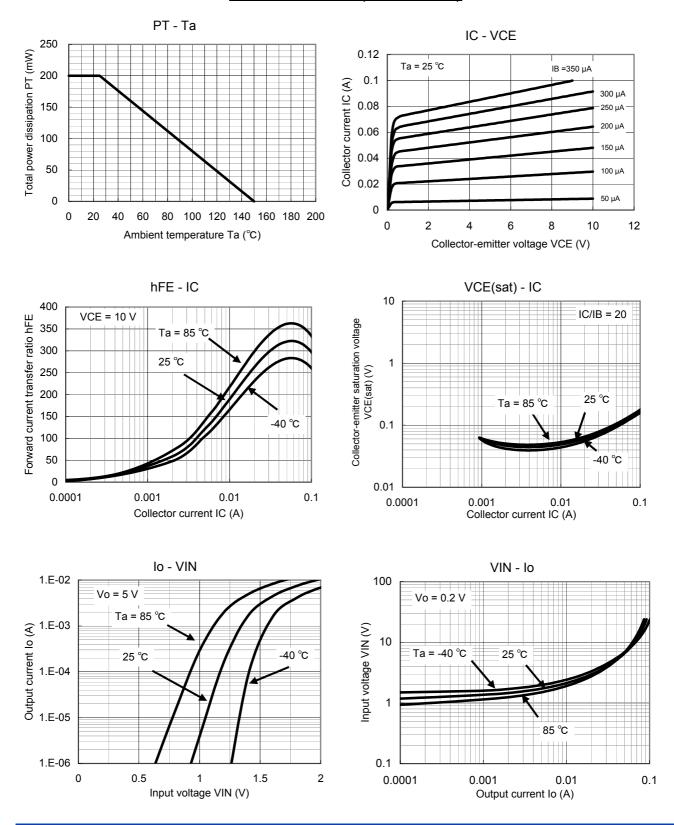
| Parameter | Symbol | Conditions | Min | Тур | Max | Unit |
|----------------------------------------------|----------|-------------------------|------|-----|------|------|
| Collector-base voltage (Emitter open) | VCBO | IC = 10 μA, IE = 0 | 50 | | | V |
| Collector-emitter voltage (Base open) | VCEO | IC = 2 mA, IB = 0 | 50 | | | V |
| Collector-base cutoff current (Emitter open) | ICBO | VCB = 50 V, IE = 0 | | | 0.1 | μA |
| Collector-emitter cutoff current (Base open) | ICEO | VCE = 50 V, IB = 0 | | | 0.5 | μA |
| Emitter-base cutoff current (Collector open) | IEBO | VEB = 6 V, IC = 0 | | | 0.2 | mA |
| Forward current transfer ratio | hFE | VCE = 10 V, IC = 5 mA | 60 | | | - |
| Collector-emitter saturation voltage | VCE(sat) | IC = 10 mA, IB = 0.5 mA | | | 0.25 | V |
| Input voltage | Vi(on) | VCE = 0.2 V, IC = 5 mA | 2.6 | | | V |
| | Vi(off) | VCE = 5 V, IC = 100 µA | | | 0.8 | V |
| Input resistance | R1 | | -30% | 22 | +30% | kΩ |
| Resistance ratio | R1/R2 | | 0.8 | 1.0 | 1.2 | - |

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors.

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Technical Data (reference)



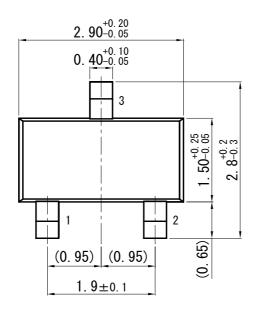
Established : 2009-10-30 Revised : 2014-03-07 Doc No. TT4-EA-11746 Revision. 2

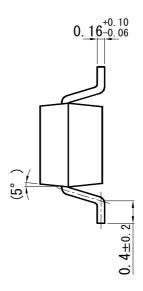


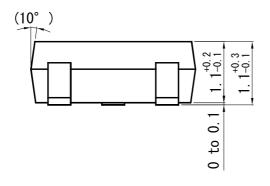
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Mini3-G3-B

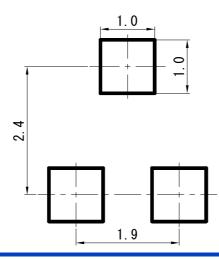
Unit: mm







Land Pattern (Reference) (Unit: mm)



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